

400V N-Channel MOSFET

Description

The MSF2N40 is a N-channel enhancement-mode MOSFET , providing the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost effectiveness. The TO-220F package is universally preferred for all commercial-industrial applications

Features

- BVDSS=400V typically @ Tj=150°C
- Low On Resistance
- Simple Drive Requirement
- · Low Gate Charge
- Fast Switching Characteristic
- RoHS compliant package

Application

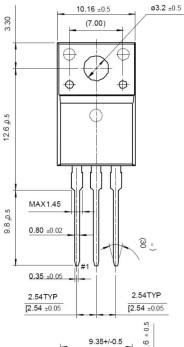
- Adapter
- Switching Mode Power Supply

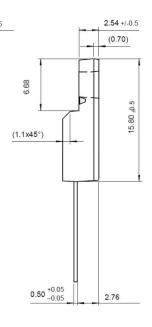
Packing & Order Information

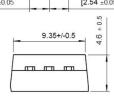
50/Tube ; 1,000/Box



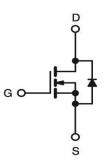








Graphic symbol



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings						
Symbol	Parameter	Value	Unit			
V _{DSS}	Drain-Source Voltage	400	V			
V _{GS}	Gate-Source Voltage	±30	V			
I _D	Drain Current -Continuous (TC=25°C)	2.0	A			
	Drain Current -Continuous (TC=100°C)	1.8	A			
I _{DM}	Drain Current Pulsed	5.4	A			
E _{AS}	Single Pulsed Avalanche Energy	100	mJ			
E _{AR}	Repetitive Avalanche Energy	10	mJ			
dv/dt	Peak Diode Recovery dv/dt	5.5	V/ns			



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Absolute Maximum Ratings					
Symbol	Parameter	Value	Unit		
TL	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	°C		
TPKG	Maximum Temperature for Soldering @ Package Body for 10 seconds	260	°C		
P _D	Total Power Dissipation(@TC = 25 °C) 44 W	24	W		
	Derating Factor above 25 °C	0.3	W/°C		
T _{STG}	Operating and Storage Temperature Range	-55 to +150	°C		
TJ	Storage Temperature	150	°C		

Note:

1. Repetitive rating; pulse width limited by maximum junction temperature.

2. I_{AS} =5.5A, V_{DD} =50V, L=8mH, V_{G} =10V, starting TJ=+25°C.

3. I_{SD}≤5.5A, dI/dt≤100A/µs, VDD≤BVDSS, starting TJ=+25°C.

Thermal characteristics (Tc=25°C unless otherwise noted)					
Symbol	Parameter	Max.	Units		
Rthjc	Typical thermal resistance	2.87	°C/W		
$R_{ extsf{ heta}JA}$	Typical thermal resistance	62.5	0/11		

* When mounted on the minimum pad size recommended (PCB Mount)

Static Characteristics					
Symbol	Test Conditions	Min	Тур.	Max.	Units
V _{GS}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2.0		4.0	V
*R _{DS(ON)}	$V_{GS} = 10 \text{ V}, I_D = 1.0 \text{ A}$		1.0	1.5	Ω
BV _{DSS}	V_{GS} = 0 V , I_{D} = 250 μA	400			V
$\Delta BV_{DSS} / \Delta T_J$	$I_D = 250 \mu A$, Referenced to $25^{\circ}C$		0.4		
I _{DSS}	$V_{DS} = 400 V$, $V_{GS} = 0 V$			1	μΑ
DSS	$V_{DS} = 320 \text{ V}$, $V_{GS} = 0 \text{ V}$, $T_C = 125^{\circ}C$			10	
I _{GSSF}	$V_{GS} = 30 \text{ V} , V_{DS} = 0 \text{ V}$			100	nA
I _{GSSR}	$V_{\rm GS}$ = -30 V , $V_{\rm DS}$ = 0 V			-100	nA

Dynamic Characteristics						
Symbol	Test Conditions	Min	Тур.	Max.	Units	
C _{ISS}			670	870	pF	
C _{OSS}	$V_{DS} = 25 \text{ V}, \text{ V}_{GS} = 0 \text{ V},$ = f = 1.0MHz		95	125	pF	
C _{RSS}			16	21	pF	



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Dynamic Characteristics					
Symbol	Test Conditions	Min	Тур.	Max.	Units
t _{d(on)}			20	50	ns
t _r	$V_{DS} = 200 \text{ V}, \text{ I}_{D} = 5.5 \text{ A},$		50	110	ns
t _{d(off)}	$R_{G} = 25 \Omega$		90	190	ns
tf			55	120	ns
Q _g	$V_{DS} = 320 \text{ V}, I_D = 5.5 \text{ A},$ - $V_{GS} = 10 \text{ V}$		25	33	nC
Q _{gs}			5.0		
Q _{gd}			10.0		

Source-Drain Diode Characteristics					
Symbol	Test Conditions	Min	Тур.	Max.	Units
I _S				2	A
I _{SM}				2.5	
V _{SD}	$I_S = 2 A$, $V_{GS} = 0 V$			1.5	V
t _{rr}	$I_{S} = 2 A$, $V_{GS} = 0 V$		220		ns
Q _{rr}	diF/dt = 100A/µs		2		μC

Notes;

1. Repetitive Rating: Pulse width limited by maximum junction temperature

2. I_{AS} =2A, V_{DD} =50V, R_{G} =25W, Starting T_{J} =25°C

3. I_{SD}≦2A, di/dt≦300A/µs,V_{DD}≦BV_{DSS}, Starting T_J=25°C

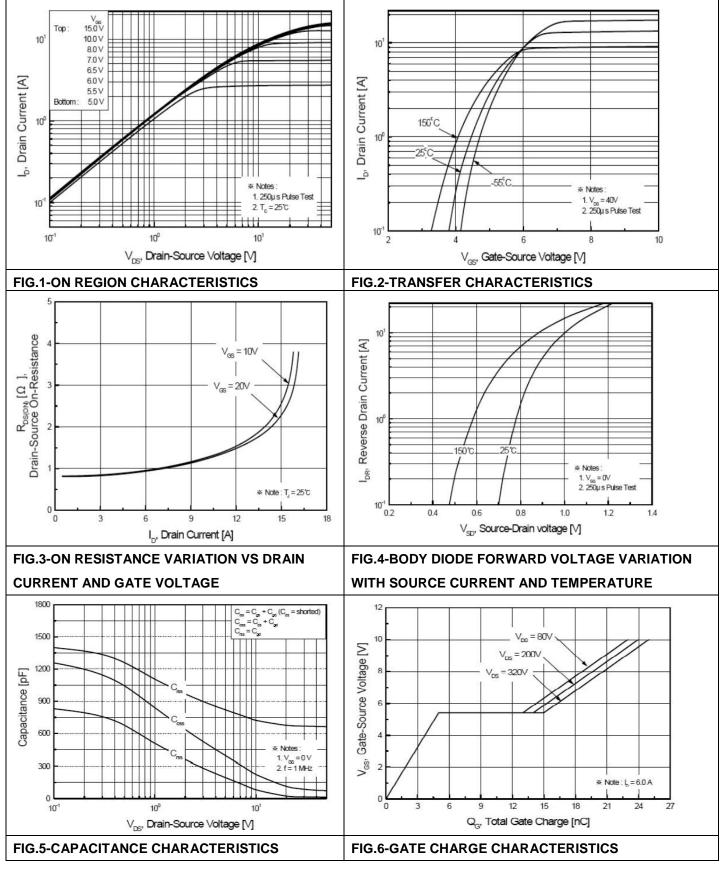
4. Pulse Test: Pulse Width ≦ 300µs, Duty Cycle≦ 2%

5. Essentially Independent of Operating Temperature



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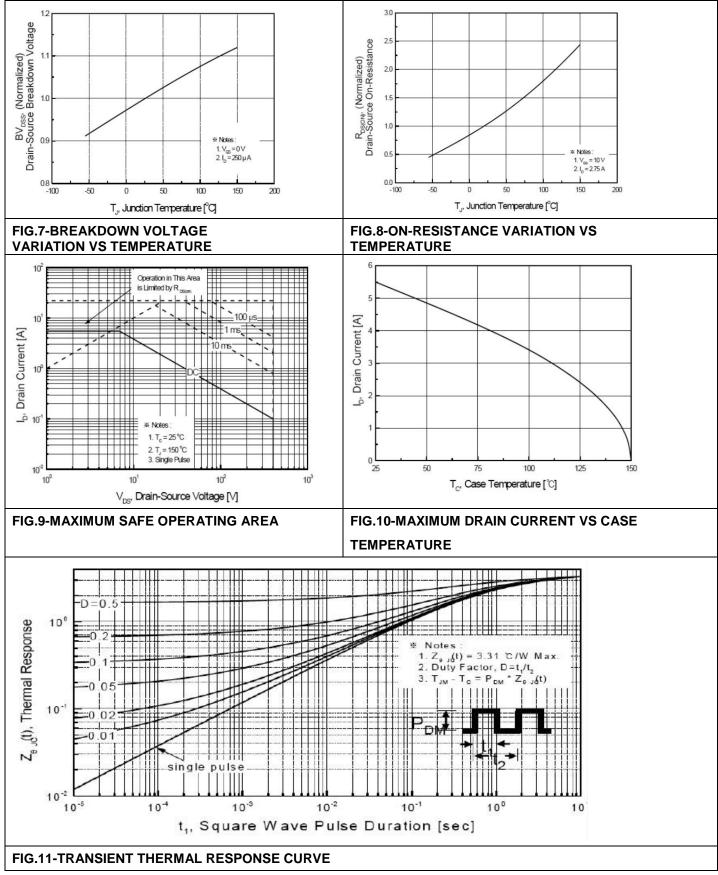
Characteristics Curve





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Characteristics Curve





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